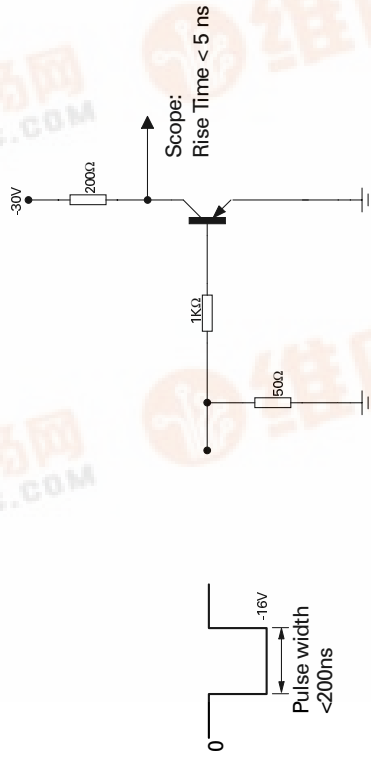


# FZT2907 FZT2907A

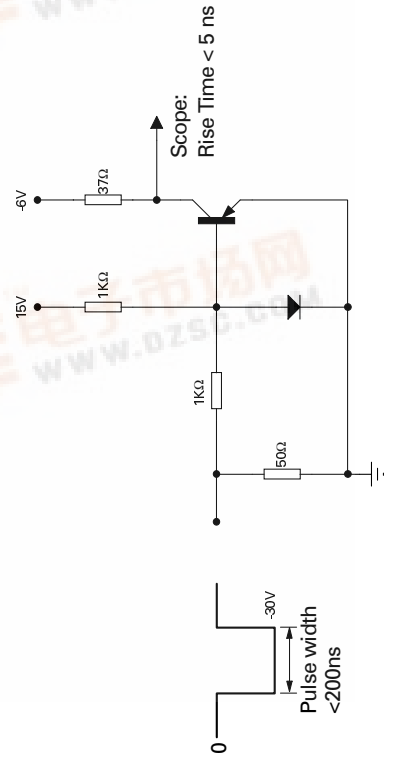
## SWITCHING CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	FMMT2907		FMMT2907A		UNIT	CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
Output Capacitance	$C_{obo}$	8	8	8	8	pF	$V_{CE}=-10\text{V}, I_E=0,$ $f=100\text{KHz}$
Input Capacitance	$C_{ibo}$	30	30	30	30	pF	$V_{BE}=-2\text{V}, I_C=0$ $f=100\text{KHz}$
Turn On Time	$t_{on}$	50	50	50	50	ns	$V_{CE}=-30\text{V}$ $I_C=150\text{mA}, I_B=-15\text{mA}$ (See Turn On Circuit)
Turn Off Time	$t_{off}$	110	110	110	110	ns	$V_{CE}=-6\text{V}, I_C=150\text{mA}$ $I_B I_B=-15\text{mA}$ (See Turn Off Circuit)

### TURN ON TIME – TEST CIRCUIT



### TURN OFF TIME – TEST CIRCUIT

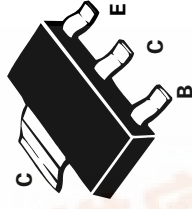


# SOT223 PNP SILICON PLANAR SWITCHING TRANSISTOR

ISSUE 4 – JUNE 1996

## FEATURES

- \* 60 Volt  $V_{CEO}$
  - \* Fast switching
- PARTMARKING DETAIL – FZT2907 – FZT2907  
FZT2907A – FZT2907A



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMT2907	FMMT2907A	UNIT
Collector-Base Voltage	$V_{CBO}$	-60	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-40	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5	-5	V
Continuous Collector Current	$I_C$	-600	-600	mA
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	$P_{tot}$	1.5	1.5	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150		$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	FZT2907		FZT2907A		UNIT	CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	-60	-60	-60	V	$I_C=-10\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	-60	-60	-60	V	$I_C=-10\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-5	-5	-5	V	$I_E=-10\mu\text{A}, I_C=0$
Collector-Emitter Cut-Off Current	$I_{CEX}$	-50	-50	-50	-50	nA	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$
Collector Cut-Off Current	$I_{CBO}$	-20	-20	-10	-10	nA	$V_{CE}=50\text{V}, I_E=0$
Base Cut-Off Current	$I_B$	-50	-50	-50	-50	nA	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-0.4	-1.6	-0.4	-1.6	V	$I_C=150\text{mA}, I_B=15\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-1.3	-2.6	-1.3	-2.6	V	$I_C=150\text{mA}, I_B=15\text{mA}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	35	75	50	100		$I_C=10\text{mA}, V_{CE}=10\text{V}$
Transition Frequency	$f_T$	100	100	100	100	MHz	$I_C=10\text{mA}, V_{CE}=10\text{V}$
		30	50	50	50		

\*Measured under pulsed conditions. Pulse width=300ms. Duty cycle  $\leq 2\%$

查询FZT2907供应商

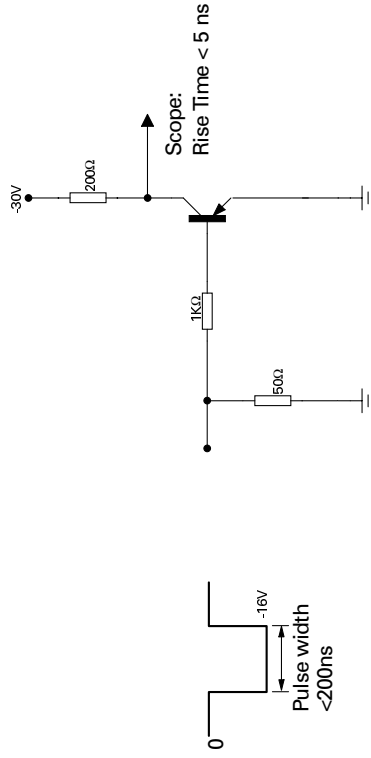
捷多邦, 专业PCB打样工厂, 24小时加急出货

# FZT2907 FZT2907A

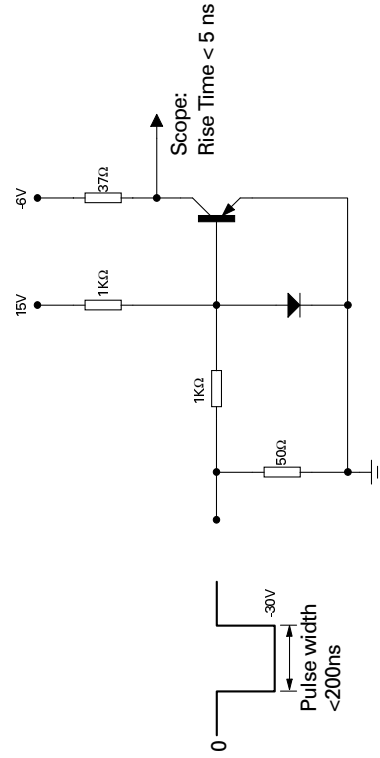
## SWITCHING CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	FMMT2907		FMMT2907A		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Output Capacitance	$C_{obo}$	8	8	8	8	pF	$V_{CE}=-10\text{V}, I_E=0,$ $f=100\text{KHz}$
Input Capacitance	$C_{ibo}$	30	30	30	30	pF	$V_{BE}=-2\text{V}, I_C=0$ $f=100\text{KHz}$
Turn On Time	$t_{on}$	50	50	50	50	ns	$V_{CE}=-30\text{V}$ $I_C=150\text{mA}, I_B=-15\text{mA}$ (See Turn On Circuit)
Turn Off Time	$t_{off}$	110	110	110	110	ns	$V_{CE}=-6\text{V}, I_C=150\text{mA}$ $I_B=I_B=-15\text{mA}$ (See Turn Off Circuit)

### TURN ON TIME – TEST CIRCUIT



### TURN OFF TIME – TEST CIRCUIT



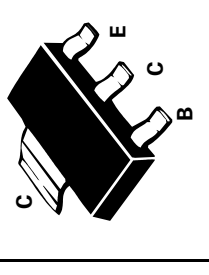
# SOT223 PNP SILICON PLANAR SWITCHING TRANSISTOR

ISSUE 4 – JUNE 1996

## FEATURES

- \* 60 Volt  $V_{CEO}$
- \* Fast switching

PARTMARKING DETAIL – FZT2907 – FZT2907  
FZT2907A – FZT2907A



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMT2907	FMMT2907A	UNIT
Collector-Base Voltage	$V_{CBO}$		-60	V
Collector-Emitter Voltage	$V_{CEO}$	-40	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5	-5	V
Continuous Collector Current	$I_C$	-600	-600	mA
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	$P_{tot}$	1.5	1.5	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150		$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	FZT2907		FZT2907A		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	-60			V	$I_C=-10\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	-60			V	$I_C=-10\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-5			V	$I_E=-10\mu\text{A}, I_C=0$
Collector-Emitter Cut-Off Current	$I_{CEX}$	-50	-50			nA	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$
Collector Cut-Off Current	$I_{CBO}$	-20	-20			nA	$V_{CE}=50\text{V}, I_E=0$
Base Cut-Off Current	$I_B$	-50	-50			nA	$V_{CE}=50\text{V}, I_E=0$ $V_{CE}=50\text{V}, I_E=0, T_{amb}=150^{\circ}\text{C}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-0.4	-1.6	-0.4	-1.6	V	$I_C=150\text{mA}, I_B=15\text{mA}^*$ $I_C=500\text{mA}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-1.3	-2.6	-1.3	-2.6	V	$I_C=150\text{mA}, I_B=15\text{mA}^*$ $I_C=500\text{mA}, I_B=50\text{mA}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	35	75	100	100		$V_{CE}=10\text{V}, V_{CE}=10\text{V}$ $I_C=10\text{mA}, V_{CE}=10\text{V}$ $I_C=150\text{mA}, V_{CE}=10\text{V}^*$ $I_C=500\text{mA}, V_{CE}=10\text{V}^*$
Transition Frequency	$f_T$	200	200			MHz	$I_C=50\text{mA}, V_{CE}=20\text{V}$ $f=100\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300ms. Duty cycle  $\leq 2\%$